

L Magafas

List of Publications by Year in descending order

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19
papers

146
citations

1307594

7
h-index

1199594

12
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19
all docs

19
docs citations

19
times ranked

111
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrical properties of a-SiC/c-Si(p) heterojunctions. Semiconductor Science and Technology, 1992, 7, 1363-1368.	2.0	40
2	Optical properties of $\hat{I}\pm$ -SiC:H thin films grown by rf sputtering. Physical Review B, 1994, 49, 8191-8197.	3.2	15
3	The effect of thermal annealing on the optical properties of a-SiC:H films. Journal of Non-Crystalline Solids, 1998, 238, 158-162.	3.1	14
4	The Dependence of Electrical and Optical Properties of RF Sputtered Amorphous Siliconâ€“Carbon Alloy Thin Films on Substrate Temperature and Hydrogen Flow Rate. Physica Status Solidi A, 1991, 126, 143-150.	1.7	12
5	The influence of metal work function on electrical properties of metal/ a-SiC:H Schottky diodes. Microelectronics Journal, 1997, 28, 107-114.	2.0	11
6	Optical Response Study of the Al/a-SiC:H Schottky Diode for Different Substrate Temperatures of the R.F. Sputtered a-SiC:H Thin Film. Active and Passive Electronic Components, 2003, 26, 63-70.	0.3	8
7	Optimization of the electrical properties of Al/a-SiC:H Schottky diodes by means of thermal annealing of a-SiC:H thin films. Microelectronics Journal, 2006, 37, 1352-1357.	2.0	8
8	Structural and optical properties of a-SiC:H thin films. Journal of Non-Crystalline Solids, 1992, 139, 146-150.	3.1	7
9	Electrical properties of annealed a-SiC:H thin films. Journal of Non-Crystalline Solids, 2007, 353, 1065-1069.	3.1	6
10	Study of optical sensors of the form A l/a-SiC:H/c-Si(n) with high sensitivity. Journal of Engineering Science and Technology Review, 2008, 1, 41-44.	0.4	5
11	Optimization of Al/a-SiC:H optical sensor device by means of thermal annealing. Microelectronics Journal, 2007, 38, 1196-1201.	2.0	4
12	Application of Physics Model in prediction of the Hellas Euro election results. Journal of Engineering Science and Technology Review, 2009, 2, 104-111.	0.4	4
13	A Study of a-SiC/C-Si(n) Isotype Heterojunctions. Active and Passive Electronic Components, 1993, 16, 55-64.	0.3	3
14	Optical response of the Al/a-SiC/c-Si(p)/Au heterojunction structure. Microelectronics Journal, 2002, 33, 761-764.	2.0	3
15	DemoscopoPhysics. Advances in Business Strategy and Competitive Advantage Book Series, 2013, , 315-327.	0.3	2
16	The Influence of Deposition Conditions on the Properties of a-SiC:H Thin Films. Materials Research Society Symposia Proceedings, 1990, 192, 589.	0.1	1
17	The a-SiC/c-Si(n) Isotype Heterojunction as a High Sensitivity Temperature Sensor. Active and Passive Electronic Components, 1998, 20, 225-234.	0.3	1
18	Application of Physics Model in prediction of the Hellas National election results. Journal of Engineering Science and Technology Review, 2009, 2, 112-117.	0.4	1

#	ARTICLE	IF	CITATIONS
19	Chaotic Behavior of the Forward I-V Characteristic of the Al/a-SiC:H/c-Si(n) Heterojunction. , 2013, , 475-479.		1